

L Number	Hits	Search Text	DB	Time stamp
-	1	(("6355561") or ("6365486")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:35
-	4817	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/30 09:50
-	81048	heated same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:17
-	246	((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale) and (heated same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:17
-	154585	precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:17
-	75	((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale) and (heated same substrate)) and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:17
-	37078	carrier adj gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:18
-	36	((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale) and (heated same substrate)) and precursor) and (carrier adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:30
-	3	("5916365").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:55
-	3	("4058430").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/27 14:55
-	233	tungsten adj hexafluoride and silicon adj wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/28 14:16
-	20738	second adj temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/30 09:52
-	2	hexamethyldisilazne	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/28 14:19
-	5749	hexamethyldisilazane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/28 14:19

-	1	(tungsten adj hexafluoride and silicon adj wafer) and hexamethyldisilazane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:27
-	1115557	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:28
-	205	(tungsten adj hexafluoride and silicon adj wafer) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:45
-	3	("5225366").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:45
-	8	5225366.URPN.	USPAT	2002/03/28 14:52
-	5	5294286.URPN.	USPAT	2002/03/28 15:03
-	0	5503105.URPN.	USPAT	2002/03/28 15:05
-	15	("4058430" "4389973" "4767494" "4845049" "4859627" "4876218" "4993357" "5060595" "5071670" "5130269" "5166092" "5225366" "5256244" "5270247" "5693139").PN.	USPAT	2002/03/28 15:06
-	15	heated adj wafer adj chuck	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/31 14:57
-	39	semiconductor adj wafer and chuck and heat and cool and robotic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/31 14:59
-	5233	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:20
-	41	second adj temperature and ((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 09:53
-	4	5130269.URPN.	USPAT	2002/08/30 09:56
-	0	micron.as. and (chemiabsorb or chemiabsorbing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:13
-	9	micron.as. and (chemisorb or chemisorbing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:14
-	6894	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:30

-	0	nh2 and h20 and ((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/07 09:30
-	128	precursor adj gas and ald	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/07 11:16
-	10	((("6627260") or ("5937300") or ("6060383") or ("6258690") or ("6596636")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:28
-	236	(438/628).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:36
-	12	(ald or atomic adj layer adj deposition) and ((438/628).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:51
-	3851	(ald or atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:51
-	1158	(metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:53
-	315	activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:53
-	255	agent and (activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:53
-	32	semiconductor and (agent and (activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/01 13:53